IXYS

HiPerFET™ Power MOSFET

Single Die MOSFET

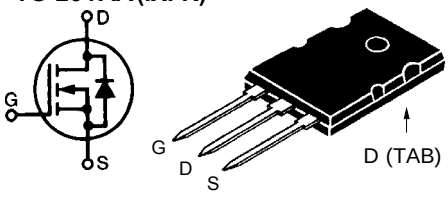
Preliminary data sheet

	V_{DSS}	I_{D25}	$R_{DS(on)}$	t_{rr}
IXFN 55N50	500V	55A	80mΩ	250ns
IXFN 50N50	500V	50A	100mΩ	250ns
IXFK 55N50	500V	55A	80mΩ	250ns
IXFK 50N50	500V	50A	100mΩ	250ns

Symbol	Test Conditions	Maximum Ratings IXFK 55N50	IXFK 50N50	IXFN 55N50	IXFN 50N50	
V_{DSS}	T_J = 25°C to 150°C		500		500	V
V_{DGR}	T_J = 25°C to 150°C		500		500	V
V_{GS}	Continuous		±20		±20	V
V_{GSM}	Transient		±30		±30	V
I_{D25}	T_C = 25°C	55	50	55	50	A
I_{DM}	T_C =25°C,	220	200	220	200	A
I_{AR}	T_C = 25°C	55	50	55	50	A
E_{AR}	T_C = 25°C		60		60	mJ
dv/dt	$I_S \le I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \le V_{DSS}$ $T_J \le 150°C$, R_G = 2 Ω		5		5	V/ns
P_D	T_C = 25°C		560		600	W
T_J			-55 ... +150			°C
T_{JM}			150			°C
T_{stg}			-55 ... +150			°C
T_L	1.6 mm (0.063 in) from case for 10 s		300		N/A	°C
V_{ISOL}	50/60 Hz, RMS t = 1 min		N/A		2500	V~
	$I_{ISOL} \le$ 1 mA t = 1 s		N/A		3000	V~
M_d	Mounting torque		0.9/6		1.5/13	Nm/lb.in.
	Terminal connection torque		N/A		1.5/13	Nm/lb.in.
Weight			10		30	g

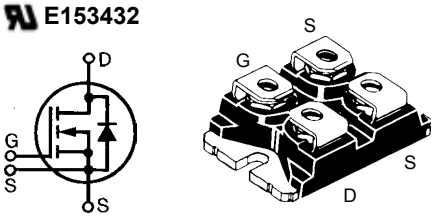
Symbol (T_J = 25°C, unless otherwise specified)	Test Conditions		Characteristic Values Min.	Typ.	Max.	
V_{DSS}	V_{GS} = 0 V, I_D = 1mA		500			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 8mA		2.5		4.5	V
I_{GSS}	V_{GS} = ±20V; V_{DS} = 0V				±200	nA
I_{DSS}	$V_{DS} = V_{DSS}$	T_J = 25°C			25	µA
	V_{GS} = 0 V	T_J = 125°C			2	mA
$R_{DS(on)}$	V_{GS} = 10 V, $I_D = 0.5 \cdot I_{D25}$	55N50			80	mΩ
	Note 1	50N50			100	mΩ

TO-264 AA (IXFK)



miniBLOC, SOT-227 B (IXFN)

E153432



G = Gate D = Drain
S = Source TAB = Drain
Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

- Easy to mount
- Space savings
- High power density

© 2002 IXYS All rights reserved

Downloaded From Oneyac.com

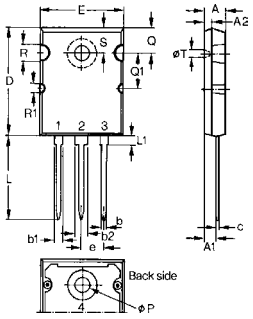
Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 • I_{D25} Note 1		45		S
C_{iss}			9400		pF
C_{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		1280		pF
C_{rss}			460		pF
$t_{d(on)}$			45		ns
t_r	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		60		ns
$t_{d(off)}$	R_G = 1 Ω (External),		120		ns
t_f			45		ns
$Q_{g(on)}$			330		nC
Q_{gs}	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		55		nC
Q_{gd}			155		nC
R_{thJC}	TO-264 AA			0.22	K/W
R_{thCK}	TO-264 AA		0.15		K/W
R_{thJC}	miniBLOC, SOT-227 B			0.21	K/W
R_{thCK}	miniBLOC, SOT-227 B		0.05		K/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
I_S	V_{GS} = 0	55N50			55	A
		50N50			50	A
I_{SM}	Repetitive;	55N50			220	A
	pulse width limited by T_{JM}	50N50			200	A
V_{SD}	I_F = 100 A, V_{GS} = 0 V	Note 1			1.5	V
t_{rr}					250	ns
Q_{RM}	I_F = 25 A, -di/dt = 100 A/µs, V_R = 100 V			1.0		µC
I_{RM}				10		A

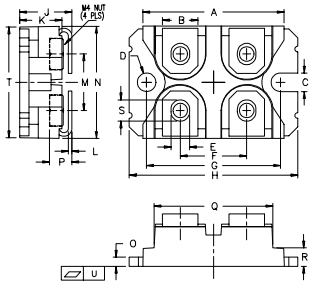
Notes: 1. Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %

TO-264 AA Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Downloaded From Oneyac.com

Figure 1. Output Characteristics at 25°C

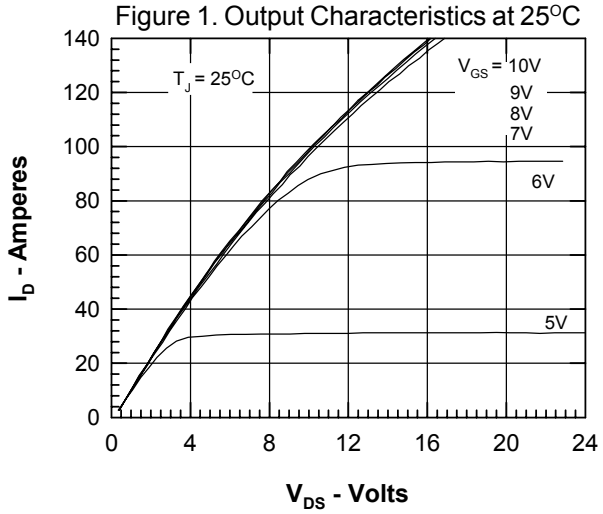


Figure 2. Output Characteristics at 125°C

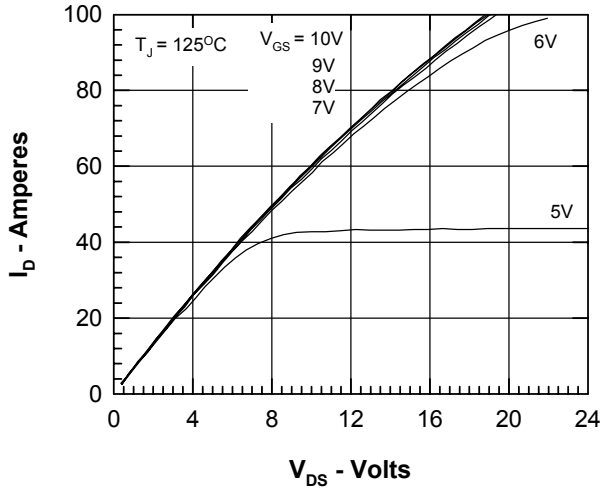


Figure 3. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. I_D

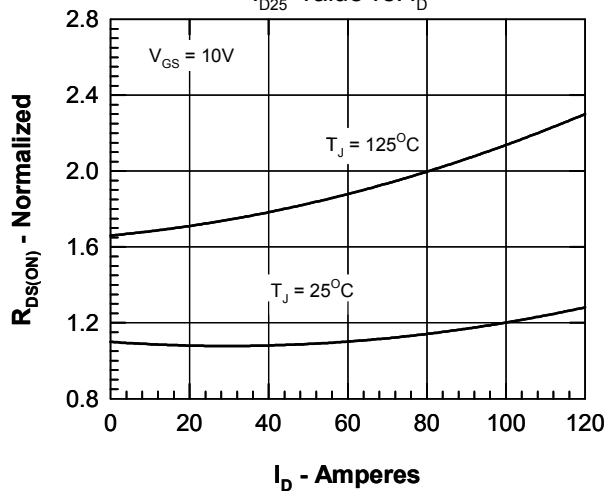


Figure 4. $R_{DS(on)}$ normalized to 0.5 I_{D25} value vs. T_J

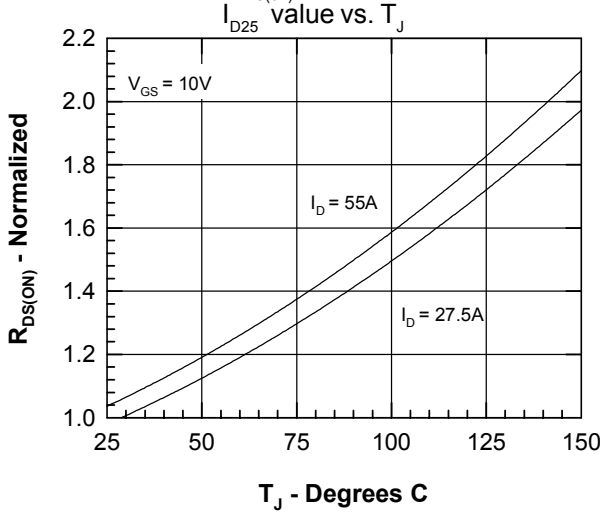


Figure 5. Drain Current vs. Case Temperature

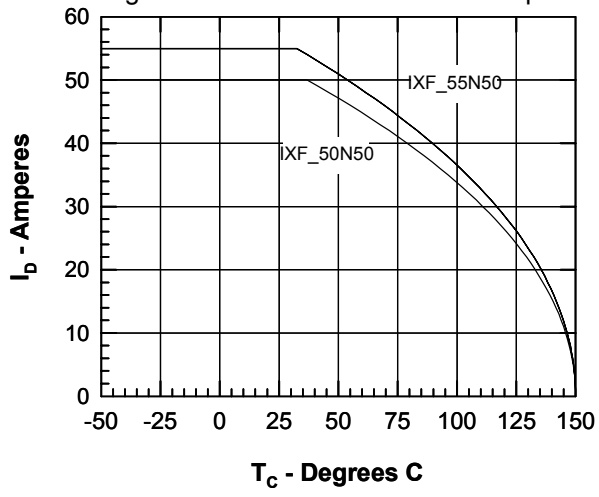
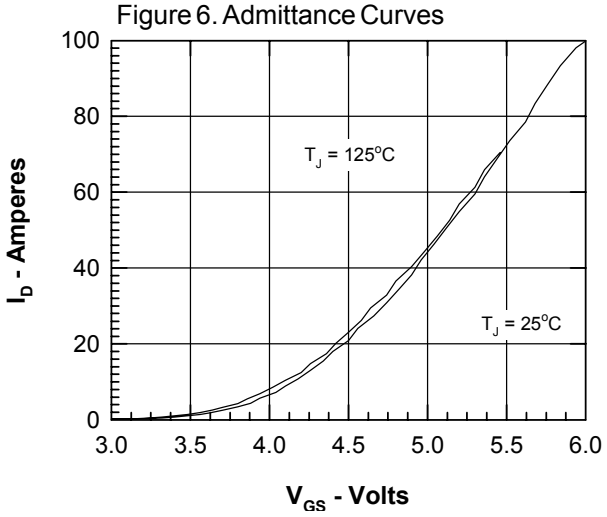


Figure 6. Admittance Curves



© 2002 IXYS All rights reserved

Downloaded From Oneyac.com

Figure 7. Gate Charge

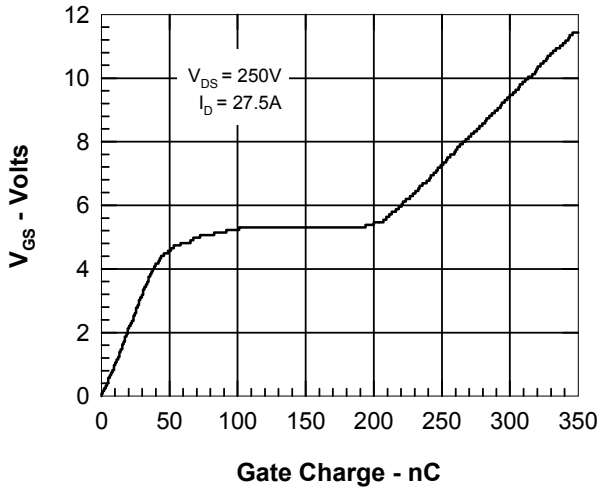


Figure 8. Capacitance Curves

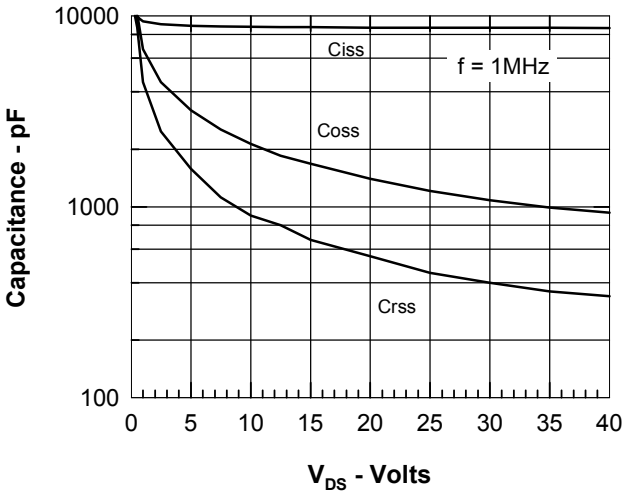


Figure 9. Forward Voltage Drop of the Intrinsic Diode

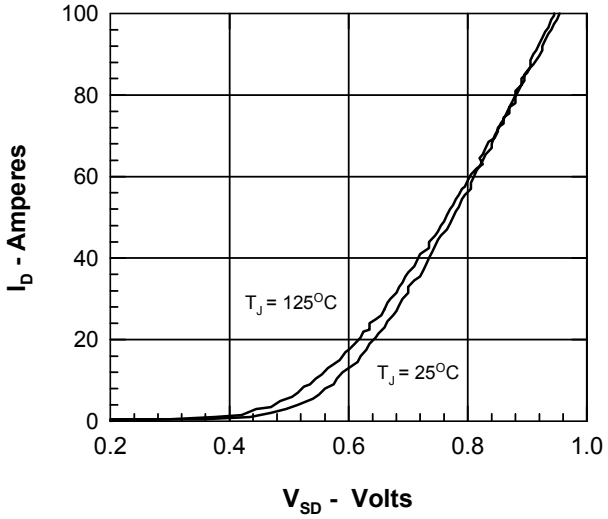
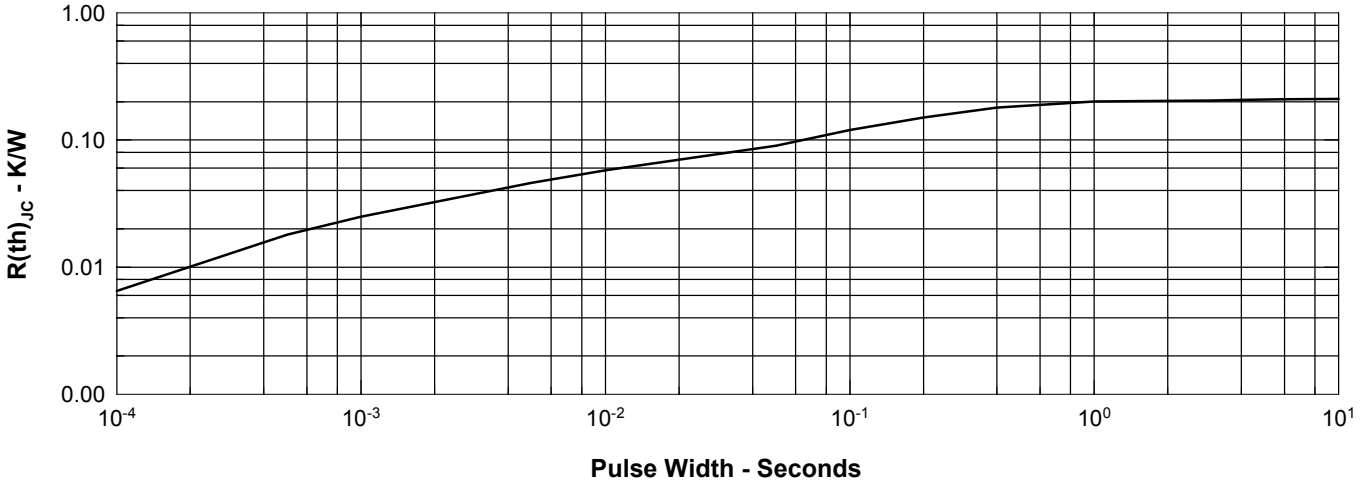


Figure 10. Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Downloaded From Oneyac.com

单击下面可查看定价，库存，交付和生命周期等信息

>>Littelfuse(美国力特)

Downloaded From Oneyac.com